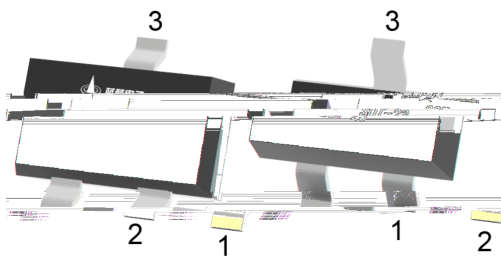
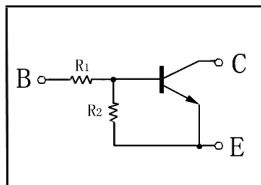


VRW056 QSQ Silicon NPN Digital transistor in a SOT-23 Plastic Package.

With built-in bias resistors, simplify circuit design, reduce a quantity of parts and manufacturing process, HF Product.

Switching applications, interface circuit and driver circuit applications.



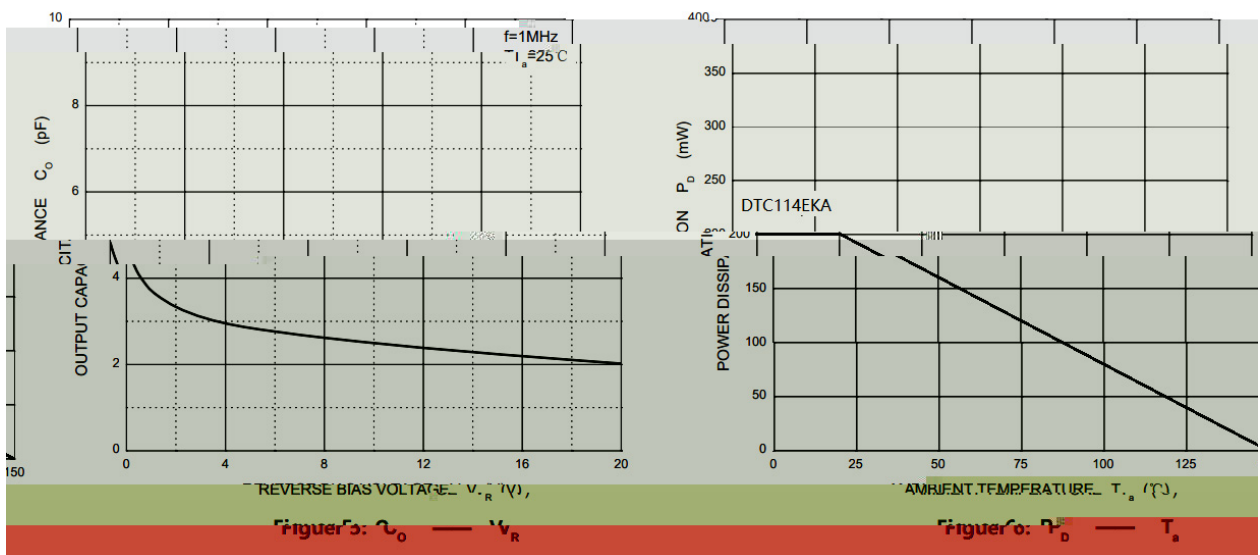
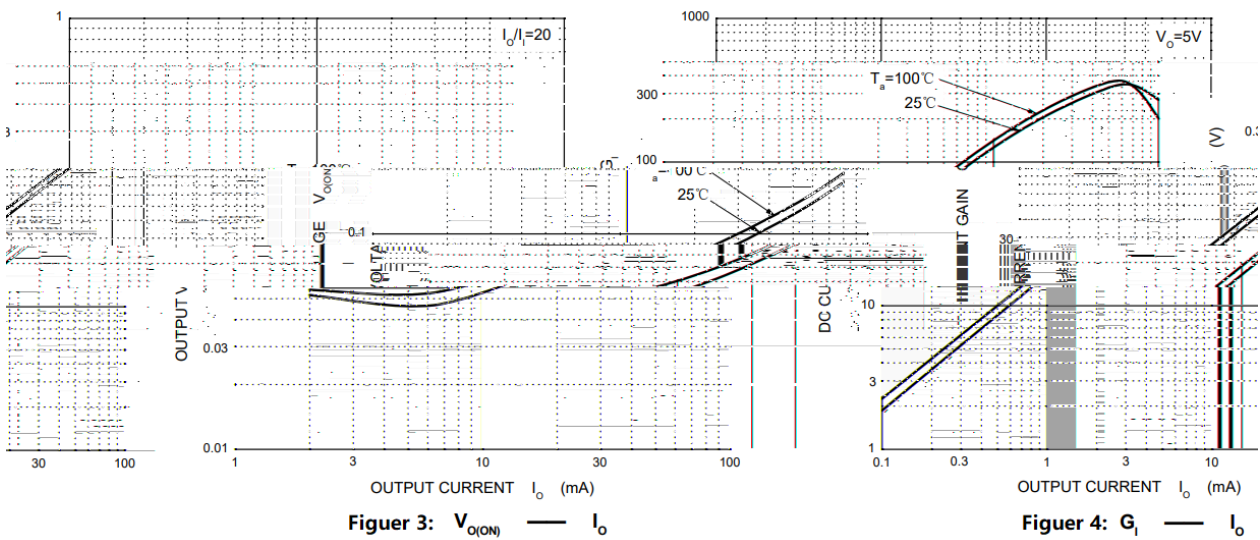
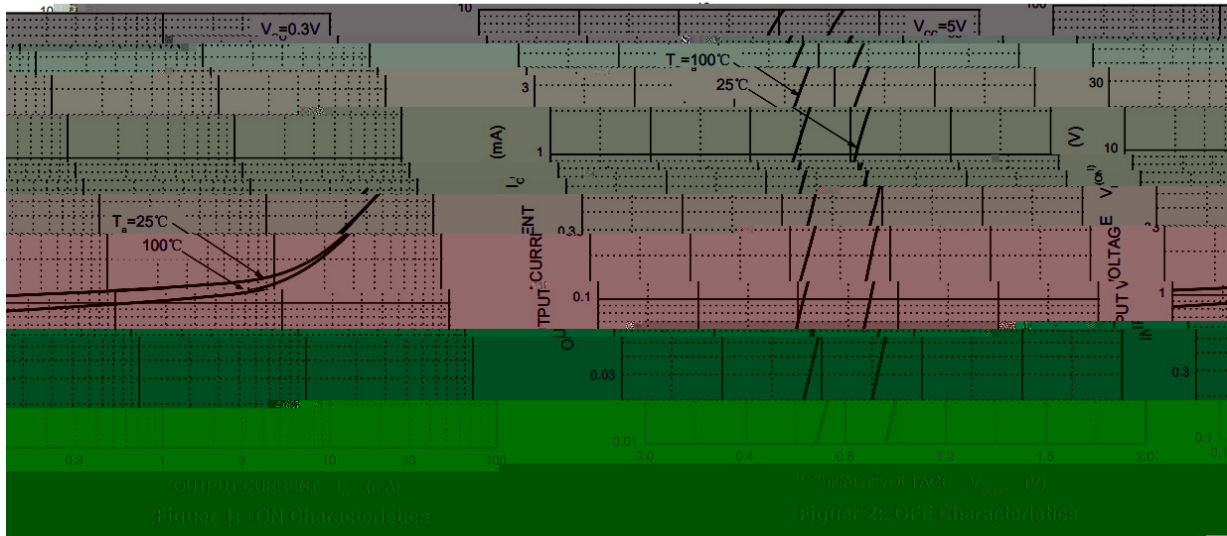
PIN 1 Base PIN 2 Emitter PIN 3 Collector

Marking

H24

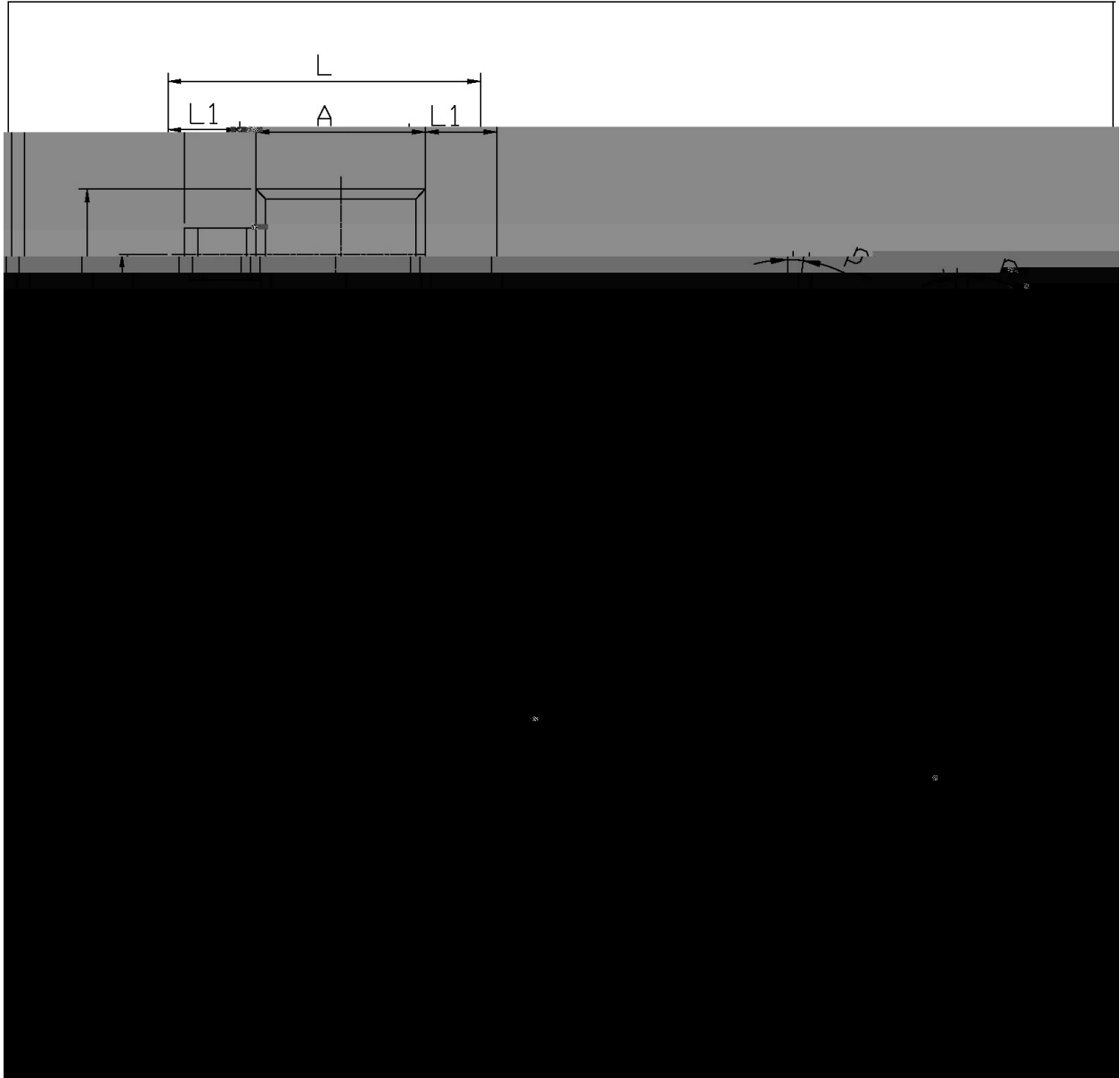
Parameter	Symbol	Rating	Unit
Supply Voltage	V_{CC}	50	V
Input Voltage	V_{IN}	-10	V
		40	V
Output Current	I_{CM}	100	mA
	I_O	50	mA
Power Dissipation	P_D	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Voltage	$V_{I(off)}$	$V_{CC}=5.0V$ $I_O=100\mu A$	0.5			V
Input Voltage	$V_{I(on)}$	$V_O=0.3V$ $I_O=10mA$			3	V
Output Voltage	$V_{O(on)}$	$I_O=10mA$ $I_I=0.5mA$			0.3	V
Input Current	I_I	$V_I=5.0V$			0.88	mA
Output Cut-off Current	$I_{O(off)}$	$V_{CC}=50V$ $V_I=0V$			0.5	μA
DC Current Gain	G_I	$V_O=5.0V$ $I_O=5.0mA$	30			
Transition Frequency	f_T	$V_O=10V$ $I_O=5.0mA$ $f=100MHz$		250		MHz
Resistance1	R_1		7	10	13	K Ω
Resistance Ratio	R_2/R_1		0.8	1	1.2	



SOT-23

单位: mm





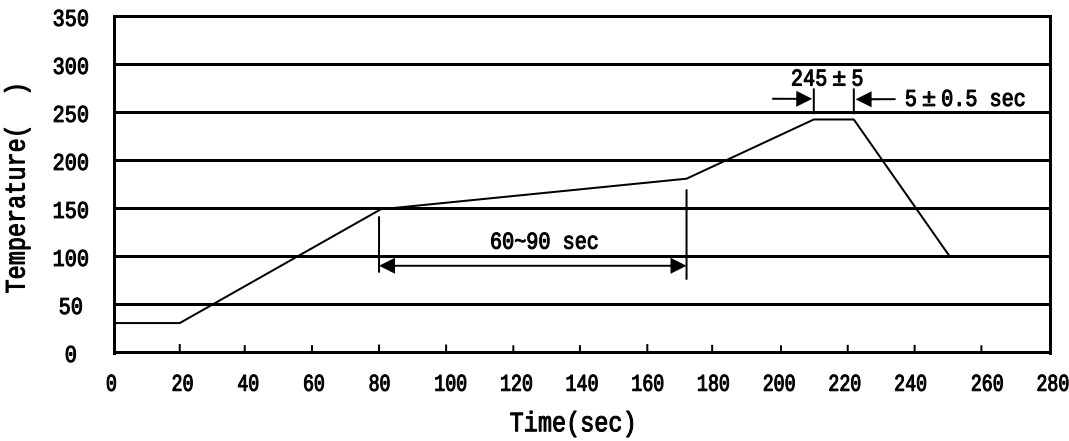
K

57

Note:

K Company Code

24 Product Type Code



- Note:
- 1

150 180%

60 90sec;

2

245 ± 5%

5 ± 0.5sec;

3

2 10%/sec.

1.Preheating:150~180%, Time:60~90sec.

2.Peak Temp.:245 ± 5%, Duration:5 ± 0.5sec.

3. Cooling Speed: 2~10%/sec.

260 ± 5%

10 ± 1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205